

Response
Serial No. 09/717,143
Attorney Docket No. 001545

REMARKS

Claims 1-3, 5 and 9 are pending. Claims 1, 5 and 9 stand allowed. Claim 2 has been amended herein. Support for the amendment is set forth below.

Applicants' Response to the Rejections under 35 U.S.C. §102:

Claims 2 and 3 stand rejected under 35 USC §102(b) as being anticipated by *Yamada et al.* (JP 11-54759). In response thereto applicants have amended claim 2 to more distinctly claim the subject matter regarded as the invention. Specifically, applicants have included the claim limitation:

... said first insulating film abutting against the one end of said gate electrode and extending in a direction perpendicular to said gate electrode along said interface.

Applicants respectfully submit that *Yamada et al.* fails to teach or otherwise suggest this limitation.

Figure 2(d) of *Yamada et al.*, discloses not only the gate insulating film 4 but also the gate insulating film 4'. Both are provided directly under the gate electrode 5 (hatched region in Fig. 2(d)).

In contrast, according to the present invention defined in amended claim 2, the first insulating film 18 shown in Fig. 8 of the present application is formed, so as to abut against the one end of gate electrode 20 (Fig. 8) and extend in a direction perpendicular to the gate electrode

20 along an interface which is positioned between a body contact region 30 (Fig. 8) and source/drain regions (25, 26 in Fig. 6(h)).

Thus, the above first insulating film 18 according to the present invention is clearly different in configuration from the second insulating film 17 formed directly under the gate electrode 20, which film 17 acts as a gate insulating film, due to the above “abutting structure”. Hence, the first insulating film 18 according to the present invention is different in constitution from the gate insulating film 4' of *Yamada et al.*

In this connection, these are distinctive differences of effects derived from the above mentioned difference in constitution. In the *Yamada et al.*'s structure, it is difficult to form the silicide (CoSi_2) layers 32 shown in Fig. 8 of the present application. This is because, when utilizing the *Yamada et al.* structure, it is difficult to electrically isolate the source/drain regions from the body contact region. Therefore, the body contact region and the source/drain regions are subject to short-circuiting, when the above silicide (CoSi_2) layers of low resistance are finally forced on the surfaces of gate electrode 5, source/drain regions 6, and body contact region 8. As a result, according to *Yamada et al.*, parasitic resistance created by the lack of the above silicide layers would be increased.

Further, according to *Yamada et al.*, it is necessary to locate the body contact region 8 far away from the source/drain regions 6 with sufficient distance, taking into account the positioning error of a mask at the time of ion implantation (corresponding to separator 21 in Fig. 7(a) of the present invention).

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Thus, according to *Yamada et al.*, undesired high resistance would be created between the body contact region 8 and source/drain regions 6, due to the elongation of the above distance. In contrast, according to the present invention per amended claim 2, the above mentioned problems are solved.

Wherefore, applicants respectfully submit that in light of the amendment to claim 2, the claim and claim 3 by nature of its dependency are not anticipated by *Yamada et al.*

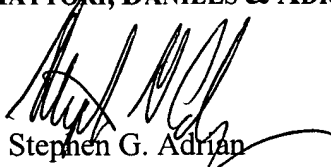
In view of the aforementioned amendments and accompanying remarks, Applicants submit that that the claims, as herein amended, are in condition for allowance. Applicants request such action at an early date.

If the Examiner believes that this application is not now in condition for allowance, the Examiner is requested to contact Applicants' undersigned attorney to arrange for an interview to expedite the disposition of this case.

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If this paper is not timely filed, Applicants respectfully petition for an appropriate extension of time. The fees for such an extension or any other fees that may be due with respect to this paper may be charged to Deposit Account No. 50-2866.

Respectfully submitted,
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